



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: 00 P 9031 US

#10/B
4/22/3
Sunder

In re the application of:)
Helmut Tews et al.) Group Art: 2813
Serial No.: 09/714,356) Examiner: Chen, Jack SJ.
Filing Date: November 16, 2000)
Title: NITROGEN IMPLANTATION USING)
A SHADOW EFFECT TO CONTROL)
GATE OXIDE THICKNESS IN)
DRAM SEMICONDUCTORS)

AMENDMENT UNDER 37 CFR \$1.115

Commissioner For Patents
P.O. Box 1450
Arlington, VA 22313-1450

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Sir:

In reply to the Office Action mailed March 11, 2003,
which rejected the claims in the above-identified patent
application, applicants respectfully request reconsideration
based on the amendments hereinafter set forth.

IN THE CLAIMS:

SUB C17
b1

1. (Twice Amended) In a process for forming dual
gate oxides for use in high performance DRAM systems or
logic circuits, the improvement comprising using a shadow
area to control gate oxide thickness at active area (AA)
corners adjacent a shallow trench isolation (STI) region,
comprising:

I) a. forming an active area by depositing over a

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